

**A T M I**

7 Commerce Drive, Danbury, CT 06810 203.794.1100 203.797.2544  
web.atmi.com info@atmi.com

## facsimile transmittance

To: Examiner Cephia D. Toomer Fax: 703-872-9310

From: Mag Chappuis Date: November 14, 2002

E-mail: [Mchappuis@atmi.com](mailto:Mchappuis@atmi.com) Pages: 17

Re: Response to November 20, 2002 cc:  
Official Action in United States  
Patent Application No. 09/551,018

---

Dear Examiner Toomer:

Please find attached a response to the November 20, 2002 Official Action in U.S. Application No. 09/551,018 for:

Silicon Reagents and Low Temperature CVD Method of Forming Silicon-Containing Gate Dielectric Materials Using Same

Including:

Response - 12 sheets  
Appendix A Cover - 1 sheet  
Appendix A Reference copy - 3 sheets  
Facsimile Transmittal Cover Sheet - 1 sheet

Please call 203-794-1100 ext. 4184 if there are any problems with this transmittal.

Maggie Chappuis  
ATMI, Inc.  
7 Commerce Drive  
Danbury, CT 06810  
203-794-1100 (telephone)  
203-797-2544 (facsimile)  
ATMI Docket: ATM-478

The document(s) accompanying this facsimile transmission contain(s) information which is confidential and/or legally privileged. The information is intended only for the use of the individual or entity named on this transmission sheet. If you are not the intended recipient, you are hereby notified that any disclosure, copying, distribution, or the taking of any action in reliance on the contents of this information is strictly prohibited, and the document(s) should be returned to the sender. If you have received this facsimile in error, please notify us by telephone immediately so that we may arrange for the return of the original documents at no cost to you.



United States Patent Application Serial No. 09/551,018  
Attorney Docket No. 478

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE****In re United States Patent Application of:****Applicants:** Chongying Xu, et al.**Serial No:** 09/551,018**Date Filed:** April 18, 2000**Title:** Silicon Reagents and Low Temperature CVD  
Method of Forming Silicon-Containing Gate  
Dielectric Materials Using Same**Group Art Unit:** 1714**Examiner:** Cephia D. Toomer**Confirmation No.:** 2050**Customer No.:** 25559**FACSIMILE TRANSMISSION CERTIFICATE**

It hereby is certified by the person identified below that this paper is being facsimile transmitted by such person to the Commissioner of Patents and Trademarks on the date specified, to the Assistant Commissioner for Patents, Washington, DC 20231, and Transmitted by Facsimile under the provisions of 37 CFR 1.6(d).

  
Maggie ChappuisApril 16, 2003  
Date of Transmission703-872-9310  
Facsimile Number

4/19/2003 MIDDLE 00000002 500860 09551018

01 FC:1201  
02 FC:125884.00 CH  
410.00 CH**AMENDMENT RESPONDING TO NOVEMBER 20, 2002 OFFICE ACTION IN U.S.  
PATENT APPLICATION NO. 09/551,018 AND  
PETITION FOR EXTENSION OF TIME UNDER 37 C.F.R. § 1.136**

Asst. Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action dated November 20, 2002, Applicant respectfully requests entry of the following Amendments and consideration of the subsequent remarks.